



Pin	Connection
1 (3)	Collector VT2
2 (4)	Base VT2
3 (5)	Emitter VT2
4 (8)	Collector VT1
5 (7)	Base VT1
6 (6)	Emitter VT1

(numbering of tare leads is indicated in brackets)

Electrical Characteristics

Parametr	Conditions	T _A	Min	Max	Units
Collector Reverse Current	U _{CB} = 20 V	+25°C	-	10	nA
		-45°C	-	10	
		+85°C	-	1000	
Reverse Emitter Current	U _{BE} = 4 V	+25°C	-	20	nA
		-45°C	-	20	
		+85°C	-	500	
Initial Collector Current	U _{CE} = 15 V, R _B = 10 ⁴ Ω	+25°C	-	20	nA
		-45°C	-	20	
		+85°C	-	1000	
Leakage Current between transistors	U _{T1T20} = 25 V	+25°C	-	10	nA
		-45°C	-	10	
		+85°C	-	300	
Static Forward Current Transfer Ratio in a Common-Emitter Circuit in Large Signal Mode	U _{CB} = 5V, f= 50 Hz, τ _u = 2 ms I _E = 1 mA	+25°C	60	180	
		-45°C	25	180	
		+85°C	60	360	
	U _{CB} = 5V, f= 50 Hz, τ _u = 2 ms I _E = 0,05 mA	+25°C	40	-	
		-45°C	20	-	
		+85°C	50	-	
Ratio of Static Forward Current Transfer Coefficients in Common Emitter Circuit in Large Signal Mode	U _{CB} = 5 V, f= 50 Hz, τ _u = 2 ms I _E = 1 mA	+25°C	0,9	-	
		-45°C	0,8	-	
		+85°C	0,8	-	
	U _{CB} = 5 V, f= 50 Hz, τ _u = 2 ms I _E = 0,05 mA	+25°C	0,88	-	
		-45°C	0,85	-	
		+85°C	0,85	-	
High Frequency Current Transfer Ratio Module	U _{CB} = 5V, I _E =3 mA, f= 10 ⁸ Hz	+25°C	3,5	-	
Forward voltage difference modulus emitter-base	U _{CB} = 5V, I _E =1 mA	+25°C	-	2,5	mV
Absolute change in modulus of emitter-base voltage difference	U _{CB} =1 V, I _E = 1mA	-45°C ÷ + 85 °C	-	2	mV
collector junction capacitance	U _{CB} = 5V, f =10 ⁷ Hz	+25°C	-	3	pF
Emitter junction capacitance	U _{BE} = 1V, f =10 ⁷ Hz	+25°C	-	4	pF
Forward voltage emitter-base transistors	U _{CE} =5V, I _E =1mA	+25°C	0,55	0,75	V

Microcircuits are made under supervision of Quality Department, checked and there correspond specification

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